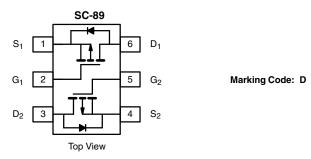




# P-Channel 60 V (D-S) MOSFET

PRODUCT	DUCT SUMMARY			
V <sub>DS (min)</sub> (V)	$R_{DS(on)}(\Omega)$	V <sub>GS(th)</sub> (V)	I <sub>D</sub> (mA)	
- 60	4 at V <sub>GS</sub> = - 10 V	- 1 to - 3.0	- 500	



Ordering Information: Si1025X-T1-GE3 (Lead (Pb)-free and Halogen-free)

### **FEATURES**

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFETs
- High-Side Switching
- Low On-Resistance: 4  $\Omega$
- Low Threshold: 2 V (typ.)
- Fast Switching Speed: 20 ns (typ.)
- Low Input Capacitance: 23 pF (typ.)
- Miniature Package
- Gate-Source ESD Protected: 2000 V
- Compliant to RoHS Directive 2002/95/EC

#### **BENEFITS**

- Ease in Driving Switches
- · Low Offset Voltage
- Low-Voltage Operation
- High-Speed Circuits
- Easily Driven Without Buffer
- Small Board Area

## **APPLICATIONS**

- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors etc.
- Battery Operated Systems
- Power Supply Converter Circuits
- Solid State Relays

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C, unless otherwise noted)					
Parameter		Symbol	5 s	Steady State	Unit
Drain-Source Voltage		V <sub>DS</sub>	- 60		V
Gate-Source Voltage		V <sub>GS</sub>	± 20		
Out! Prois Outst (T. 450.00)	T <sub>A</sub> = 25 °C	I <sub>D</sub>	- 200	- 190	A
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> = 85 °C		- 145	- 135	
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	- 650		mA
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	- 450	- 380	
M · D D · · · · · · · · · · · · · · · ·	T <sub>A</sub> = 25 °C	P <sub>D</sub>	250	ma\\\/	
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 85 °C		145	130	mW
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150		°C
Gate-Source ESD Rating (HBM, Method 3015)		ESD	2000		V

#### Notes:

- a. Surface mounted on FR4 board.
- b. Pulse width limited by maximum junction temperature.

ROHS COMPLIANT HALOGEN FREE

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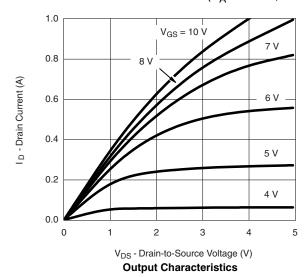
Parameter	Symbol	Test Conditions Min.		Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	urce Breakdown Voltage $V_{DS}$ $V_{GS} = 0 \text{ V}, I_D = -10 \mu\text{A}$		- 60			V	
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = -0.25 \text{ mA}$	- 1		- 3.0	V	
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 10 V		± 200			
		$V_{DS} = 0 \text{ V}, V_{GS} = \pm 5 \text{ V}$			± 100	A	
	I <sub>DSS</sub>	V <sub>DS</sub> = - 50 V, V <sub>GS</sub> = 0 V			- 25	nA	
Zero Gate Voltage Drain Current		$V_{DS} = -50 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 85 ^{\circ}\text{C}$			- 250	1	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = - 10 V, V <sub>GS</sub> = - 4.5 V	- 50			- mA	
		V <sub>DS</sub> = - 10 V, V <sub>GS</sub> = - 10 V	- 600				
		V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 25 mA			8		
Drain-Source On-Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 500 mA			4	Ω	
		V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 500 mA, T <sub>J</sub> = 125 °C			6		
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = - 10 V, I <sub>D</sub> = - 100 mA		100		mS	
Diode Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>S</sub> = - 200 mA, V <sub>GS</sub> = 0 V			- 1.4	V	
Dynamic <sup>b</sup>							
Total Gate Charge	Qg			1.7			
Gate-Source Charge	$Q_{gs}$	$V_{DS} = -30 \text{ V}, V_{GS} = -15 \text{ V}, I_{D} \cong -500 \text{ mA}$		0.26		nC	
Gate-Drain Charge	Q <sub>gd</sub>			0.46			
Input Capacitance	C <sub>iss</sub>			23			
Output Capacitance	C <sub>oss</sub>	$V_{DS} = -25 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		10		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			5			
Switching <sup>b, c</sup>					•		
Turn-On Time	t <sub>ON</sub>	$V_{DD} = -25 \text{ V}, R_L = 150 \Omega, I_D \cong -165 \text{ mA},$		20			
Turn-Off Time	t <sub>OFF</sub>	$V_{GEN} = -10 \text{ V}, R_g = 10 \Omega$		35		ns	

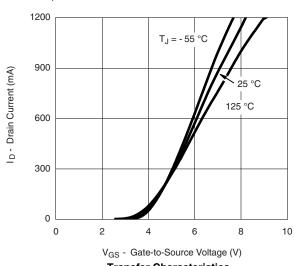
#### Notes:

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. For DESIGN AID ONLY, not subject to production testing.
- c. Switching time is essentially independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

## TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)

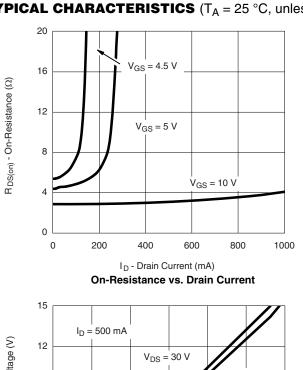


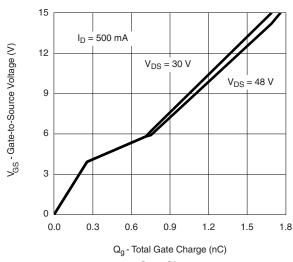


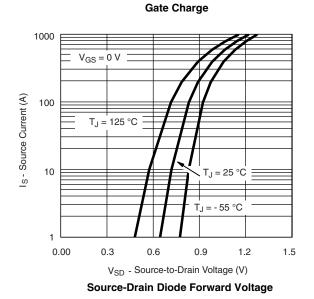
**Transfer Characteristics** 

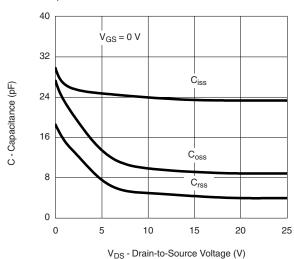


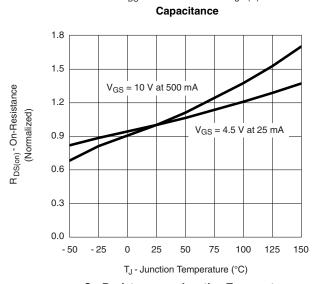
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)

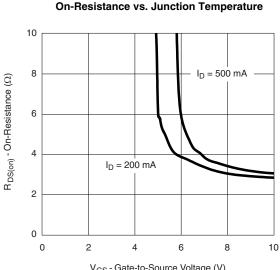










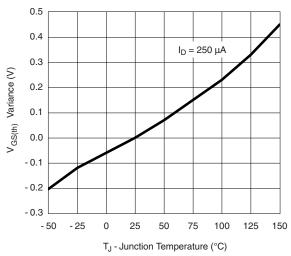


V<sub>GS</sub> - Gate-to-Source Voltage (V) On-Resistance vs. Gate-to-Source Voltage

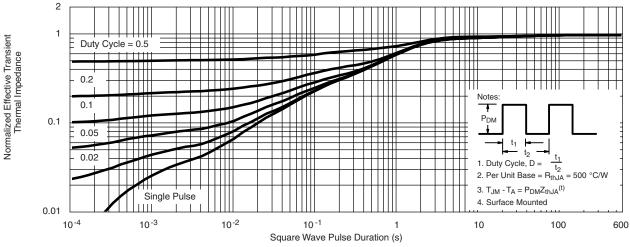
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## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



### **Threshold Voltage Variance Over Temperature**

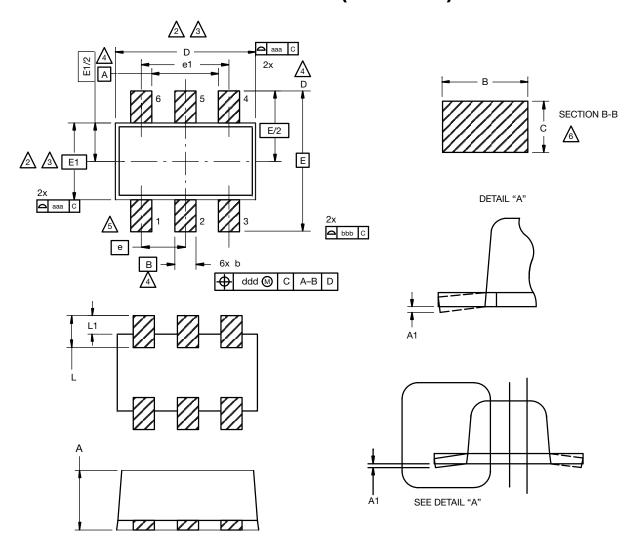


Normalized Thermal Transient Impedance, Junction-to-Ambient

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg?71433">www.vishay.com/ppg?71433</a>.



# **SC-89 6-Leads (SOT-563F)**



## Notes

1. Dimensions in millimeters.

Dimension D does not include mold flash, protrusions or gate burrs. Mold flush, protrusions or gate burrs shall not exceed 0.15 mm per dimension E1 does not include interlead flash or protrusion, interlead flash or protrusion shall not exceed 0.15 mm per side.

Dimensions D and E1 are determined at the outmost extremes of the plastic body exclusive of mold flash, the bar burrs, gate burrs and interlead flash, but including any mismatch between the top and the bottom of the plastic body.

ADatums A, B and D to be determined 0.10 mm from the lead tip.

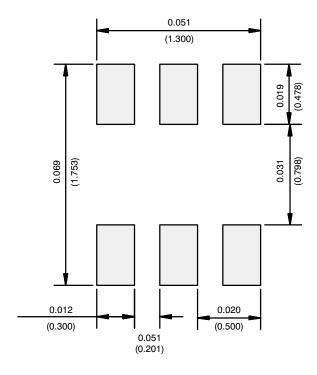
A Terminal numbers are shown for reference only.

These dimensions apply to the flat section of the lead between 0.08 mm and 0.15 mm from the lead tip.

DIM.		MILLIMETERS		
	MIN.	NOM.	MAX.	
Α	0.56	0.58	0.60	
A1	0	0.02	0.10	
b	0.15	0.22	0.30	
С	0.10	0.14	0.18	
D	1.50	1.60	1.70	
E	1.50	1.60	1.70	
E1	1.15	1.20	1.25	
е	0.45	0.50	0.55	
e1	0.95	1.00	1.05	
L	0.25	0.35	0.50	
L1	0.10	0.20	0.30	
C14-0439-Rev. C, 11-Aug-14 DWG: 5880				



## **RECOMMENDED MINIMUM PADS FOR SC-89: 6-Lead**



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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